onsemi

2-Input NAND Schmitt-Trigger with Open Drain Output

MC74VHC1G135

The MC74VHC1G135 is a single gate CMOS Schmitt NAND trigger with an open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered 3-state output which provides high noise immunity and stable output.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when $V_{CC} = 0$ V and when the output voltage exceeds V_{CC} . These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 4.9 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- IOFF Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A, SC-74A, SOT-553, SOT-953 and UDFN6 Packages
- Chip Complexity < 100 FETs
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



Figure 1. Logic Symbol



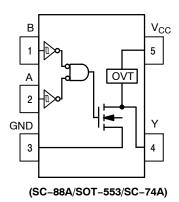
MARKING DIAGRAMS

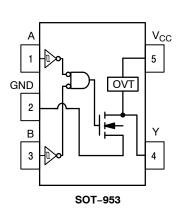
	SC-88A DF SUFFIX CASE 419A	Л П ХХМ• о •
- AND	SC-74A DBV SUFFIX CASE 318BQ	
2.00 F	SOT-553 XV5 SUFFIX CASE 463B	XX M• • •
	SOT-953 P5 SUFFIX CASE 527AE	
	UDFN6 1.45 x 1.0 CASE 517AQ	● XM
Ŷ	UDFN6 1.0 x 1.0 CASE 517BX	1 • X M
XX M	= Specific Device = Date Code* = Pb-Free Packa	
-	crodot may be in eith e orientation and/or	

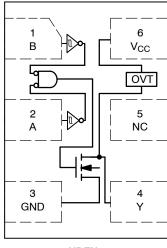
vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 7 of this data sheet.







UDFN6

Figure 2. Pinout (Top View)

PIN ASSIGNMENT (SOT-953)

PIN ASSIGNMENT (SC-88A/SOT-553/SC-74A)

Pin	Function
1	В
2	A
3	GND
4	Y
5	V _{CC}

Pin	Function
1	А
2	GND
3	В
4	Y
5	V _{CC}

PIN ASSIGNMENT (UDFN)

Pin	Function
1	В
2	А
3	GND
4	Y
5	NC
6	V _{CC}

FUNCTION TABLE

Ing	Output	
Α	В	Y
L	L	Z
L	Н	Z
Н	L	Z
Н	н	L

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
V _{OUT}	Tri	e (High or Low State) -State Mode (Note 1) wn Mode (V _{CC} = 0 V)	$\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } +6.5 \\ -0.5 \text{ to } +6.5 \end{array}$	V
Ι _{ΙΚ}	DC Input Diode Current	V _{IN} < GND	-20	mA
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±25	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC-88A SC-74A SOT-953 UDFN6	377 320 254 154	°C/W
P _D	Power Dissipation in Still Air	SC-88A SC-74A SOT-953 UDFN6	332 390 491 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating O:	kygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3) C	Human Body Model harged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Applicable to devices with outputs that may be tri-stated.

Applicable to devices with outputs that may be in-stated,
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.

4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
Vout	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode Power-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0 0	No Limit No Limit No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	Т	A = 25°	C	-40°C ≤ .	T _A ≤ 85°C	–55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Input Threshold Voltage		3.0 4.5 5.5	- - -	2.0 3.0 3.6	2.2 3.15 3.85	- -	2.2 3.15 3.85	- -	2.2 3.15 3.85	V
V _{T-}	Negative Input Threshold Voltage		3.0 4.5 5.5	0.9 1.35 1.65	1.5 2.3 2.9		0.9 1.35 1.65		0.9 1.35 1.65		V
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.85 1.05 1.20	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	V
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	2.0 3.0 4.5	- - -	0.0 0.0 0.0	0.1 0.1 0.1	- -	0.1 0.1 0.1	- -	0.1 0.1 0.1	V
		I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5		-	0.36 0.36	-	0.44 0.44	-	0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	-	-	±0.1	-	±1.0	-	±1.0	μΑ
ICC	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	-	1.0	-	20	-	40	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0.0	-	-	1.0	-	10	-	10	μΑ

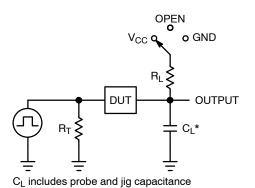
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

				Т	A = 25°	0	–40°C ≤ 1	Γ _A ≤ 85°C	–55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PZL}	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	-	7.6	11.9	-	14.0	-	16.1	ns
	(A or B) to Y (Figures 3 and 4)	C _L = 50 pF		-	10.1	15.4	-	17.5	-	19.6	
		C _L = 15 pF	4.5 to 5.5	-	4.9	7.7	-	9.0	-	10.3	1
		C _L = 50 pF		-	6.4	9.7	-	11.0	-	12.3	
t _{PLZ}	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	-	7.6	11.9	-	14.0	-	16.1	ns
	(A or B) to Y (Figures 3 and 4)	C _L = 50 pF		-	10.1	15.4	-	17.5	-	19.6	
		C _L = 15 pF	4.5 to 5.5	-	4.9	7.7	-	9.0	-	10.3	
		C _L = 50 pF		-	6.4	9.7	-	11.0	-	12.3	
C _{IN}	Maximum Input Capacitance			1	5.0	10	-	10	-	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 5)	16.0	pF

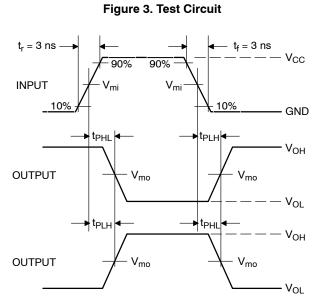
5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



 R_T is Z_{OUT} of pulse generator (typically 50 Ω) f = 1 MHz

Test	Switch Position	C _L , pF	R_L, Ω
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	Х
t _{PLZ} / t _{PZL}	V _{CC}		1 k
t _{PHZ} / t _{PZH}	GND		1 k

X = Don't Care



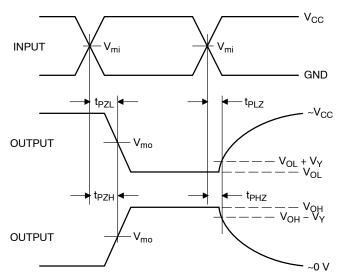


Figure 4. Switching Waveforms

		V _m o		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

ORDERING INFORMATION

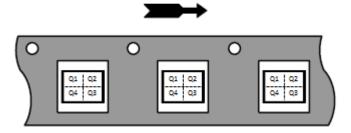
Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
MC74VHC1G135DFT1G (Contact onsemi)	SC-88A	VZ	Q2	3000 / Tape & Reel
MC74VHC1G135DFT2G (Contact onsemi)	SC-88A	VZ	Q4	3000 / Tape & Reel
MC74VHC1G135DFT2G-Q* (Contact onsemi)	SC-88A	VZ	Q4	3000 / Tape & Reel
MC74VHC1G135DBVT1G	SC-74A	VZ	Q4	3000 / Tape & Reel
MC74VHC1G135XV5T2G (Contact onsemi)	SOT-553	TBD	Q4	4000 / Tape & Reel
MC74VHC1G135P5T5G (Contact onsemi)	SOT-953	TBD	Q2	8000 / Tape & Reel
MC74VHC1G135MU1TCG (Contact onsemi)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
MC74VHC1G135MU3TCG (Contact onsemi)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL

Direction of Feed

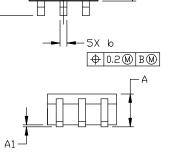


PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



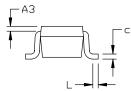
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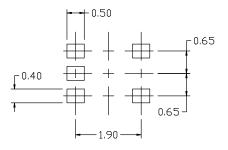
Е

е

E1

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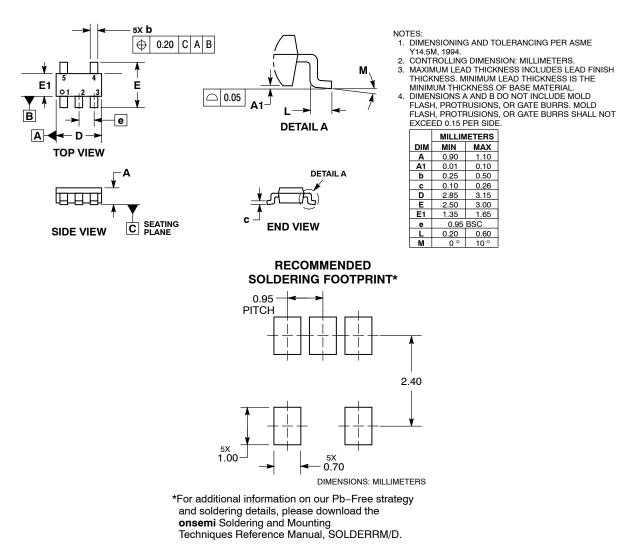
RECOMMENDED

MOUNTING FOOTPRINT * For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DIM	MILLIMETERS			
INIT	MIN,	NDM.	MAX.	
A	0.80	0.95	1.10	
A1			0.10	
A3	0.20 REF			
b	0.10	0.20	0.30	
С	0.10		0.25	
D	1.80	2.00	5.50	
E	2.00	2.10	5.50	
E1	1.15	1.25	1.35	
e	0.65 BSC			
L	0.10	0.15	0.30	

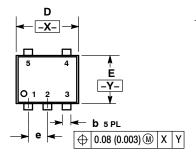
PACKAGE DIMENSIONS

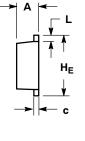
SC-74A CASE 318BQ ISSUE B



PACKAGE DIMENSIONS

SOT-553, 5 LEAD CASE 463B ISSUE C



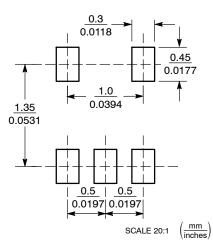


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

THICKNESS OF BASE MATERIAL.	

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е		0.50 BSC 0.020 BSC)	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

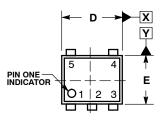
SOLDERING FOOTPRINT*



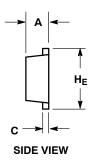
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

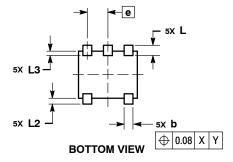
PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E



TOP VIEW

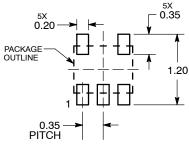




- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
Е	0.75	0.80	0.85	
e	0.35 BSC			
HE	0.95	1.00	1.05	
L	0.175 REF			
L2	0.05	0.10	0.15	
L3			0.15	

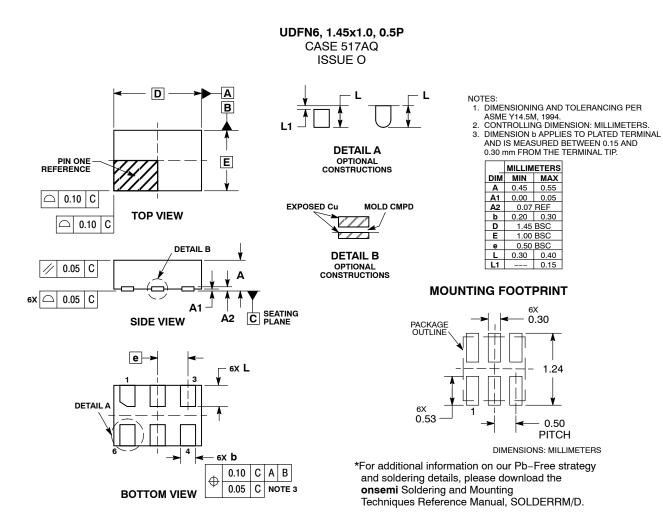
SOLDERING FOOTPRINT*



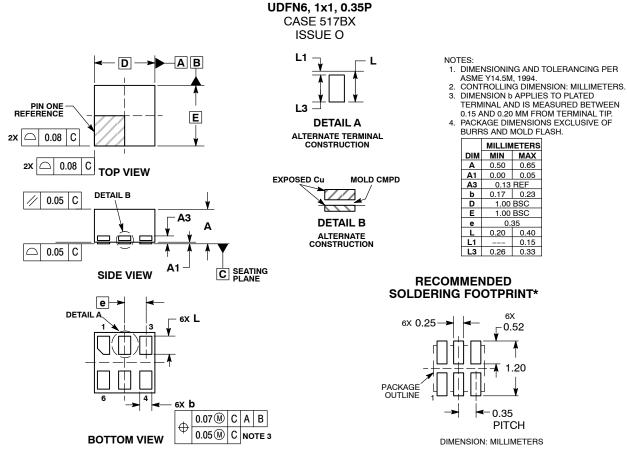
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



PACKAGE DIMENSIONS



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